

The following replacement claims are respectfully submitted:

*Sub C1*  
*a1*

1. (Amended) A method for manufacturing a capacitor of a semiconductor device, comprising:

- forming a storage electrode over a semiconductor substrate;
- forming a high dielectric layer over the storage electrode;
- forming a plate electrode over the high dielectric layer;
- performing a first post-annealing of the semiconductor substrate under an inert atmosphere at a first temperature; and
- performing a second post-annealing of the semiconductor substrate, after the first post-annealing, at a second temperature lower than the first temperature, the first and second post-annealings being performed in-situ.

*a2*  
*Cm7*  
*only B1*

9. (Amended) A method for manufacturing a capacitor of a semiconductor device, comprising:

- forming a storage electrode over a semiconductor substrate;
- forming a high dielectric layer over the storage electrode;
- forming a plate electrode over the high dielectric layer;
- performing a first post-annealing of the semiconductor substrate under an inert atmosphere; and
- performing a second post-annealing of the semiconductor substrate, after the first post-annealing, at a second temperature lower than the first temperature,

*A2 Canceled*  
the first and second post-annealings being performed after the forming of the plate electrode.

*A3 Sub C3*  
12. (Amended) A method for manufacturing a capacitor of a semiconductor device, comprising:  
forming a storage electrode over a semiconductor substrate;  
forming a high dielectric layer over the storage electrode;  
forming a plate electrode over the high dielectric layer;  
performing a first post-annealing of the semiconductor substrate under an inert atmosphere at a first temperature;  
performing a second post-annealing of the semiconductor substrate, after the first post-annealing, at a second temperature lower than the first temperature; and  
forming an interdielectric layer over the plate electrode,  
the first and second post-annealings being performed after the forming of the interdielectric layer.

*A4 Sub Cmt*  
15. (Amended) A method for manufacturing a capacitor of a semiconductor device in which a storage electrode, a high dielectric layer, a plate electrode, and an interdielectric layer are sequentially formed on a semiconductor substrate, further comprising:  
performing a first post-annealing of the semiconductor substrate under an inert

*Sub C4*  
*Off*  
*Emad*  
atmosphere at a first temperature; and

performing a second post-annealing of the semiconductor substrate, after the

first post-annealing, at a second temperature lower than the first temperature,

the first and second post-annealings being performed after forming of the plate

electrode.

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